Class Subclass ISSUE CLASSIFICATION	U:S.U	TILITY Pa	tent Appl	estion	PA	NT NUMBER
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		Figs. Drwg.	Print Fig.	Total Claims	Print Clai	m for O.G.
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The term of this patent shall to extend beyond the expiration date U.S. Patent: No. 2017/19.5.32	(Assistant Examiner) (Date)					
	(Primary E	xaminer)	(Date)	JS Amount Due	SUE FEE Date	Paid
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ARNING: Information disclosed herein may be restri session outside the U.S. Patent & Tradema PTO-436A	cted. Unauthorized d	isclosure may be pro o authorized employe	Contract to a second	olted States Code Title	35, Sections 122,	181 and 368

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